MSKSEMI 美森科













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TSS

MOV

GDT

 PLED

SB10200L-MS

Product specification





Features

- EXTREMELY LOW VF
- LOW STORED CHARGE, MAJORITY CARRIER CONDUCTION
- LOW POWER LOSS / HIGH EFFICIENCY
- UL 94V0 FLAME RETARDANT EPOXY MOLDING COMPOUND
- HALOGENFREE

MECHANICAL DATA

CASE: TRANSFER MOLDED

• LEADS: SOLDERABLE PER MIL-STD-202, METHOD 208

POLARITY: AS MARKED

WEIGHT: 0.095GRAMS(APPROXIMATELY)

Reference News

| TO-277 | Schematic Diagram | Marking |
|--------|------------------------|----------|
| 3 1 | Cathode & Heatsink 2 0 | SB10200L |

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

RATINGS AT 25. C AMBIENT TEMPERATURE UNLESS OTHERWISE SPECIFIED SINGLE PHASE, HALF WAVE, 60 HZ, RESISTIVE OR INDUCTIVE LOAD. FOR CAPACITIVE LOAD, DERATE CURRENT BY 20%

| RATINGS | SYMBOL | SB10200L | UNITS |
|--|------------------|---------------|-------|
| MAXIMUM RECURRENT PEAK REVERSE VOLTAGE | V _{RRM} | 200 | V |
| MAXIMUM RMS VOLTAGE | V _{RMS} | 140 | V |
| MAXIMUM DC BLOCKING VOLTAGE | V _{DC} | 200 | V |
| MAXIMUM AVERAGE FORWARD RECTIFIED CURRENT SEE FIG.1 PER LEG | lo | 10 | А |
| PEAK FORWARD SURGE CURRENT, 8.3ms SINGLE HALF SINE-WAVE SUPERIMPOSED ON RATED LOAD PER LEG | I _{FSM} | 250 | А |
| STORAGE TEMPERATURE RANGE | T _{STG} | - 65 TO + 150 | ∫ ℃ |
| OPERATING JUNCTION TEMPERATURE RANGE | T₃ | - 55 TO + 175 | J. C. |



ELECTRICAL CHARACTERISTICS

| CHARACTERISTICS | | SYMBOL | SB10200L | UNITS |
|--|---|----------------|----------|-------|
| MAXIMUM FORWARD VOLTAGEAT I _F = 10A | T₁=25°C | | 0.75 | |
| TYPICAL | $T_{\text{\tiny J}} = 25^{\circ}\text{C}$ | | 0.72 | |
| TYPICAL Reverse Recovery Time | | VF | 1 | |
| TYPICAL FORWARD VOLTAGE AT I _F = 5A | T₃=125°C | | 0.55 | V |
| TYPICAL FORWARD VOLTAGE AT I _F = 10 A | T₁=125°C | | 0.65 | |
| MAXIMUM REVERSE CURRENT AT 25°C PER LEG | (NOTE 1) | I _R | 5 | uA |
| MAXIMUM REVERSE CURRENT AT 125℃PER LEG (NOTE 1) | | I _R | 2 | mA |

THERMAL CHARACTERISTICS (Tc = 25°C UNLESS OTHERWISE NOTED)

| PARAMETER | SYMBOL | SB10200L | UNITS |
|--|--------|----------|-------|
| TYPICAL THERMAL RESISTANCE JUNCTION TO CASE PER LEG | Rθjc | 23 | °C/W |

NOTES: 1. PULSE TEST: 300µS PULSE WIDTH, 1% DUTY CYCLE.



RATINGSAND CHARACTERISTIC CURVES OF SB10200L-MS

FIG. 1-FORWARD CURRENT DERATING CURVE

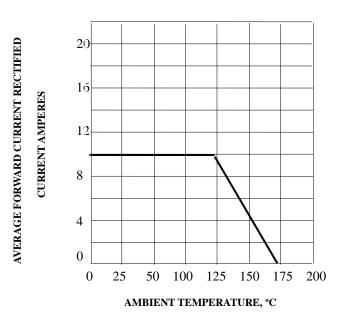


FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE RATING

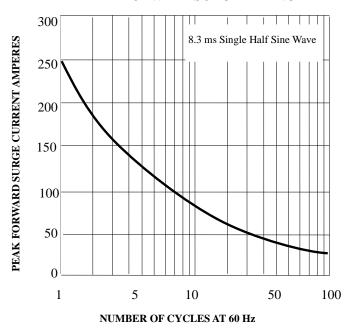


FIG. 3- TYPICAL REVERSE CHARACTERISTICS

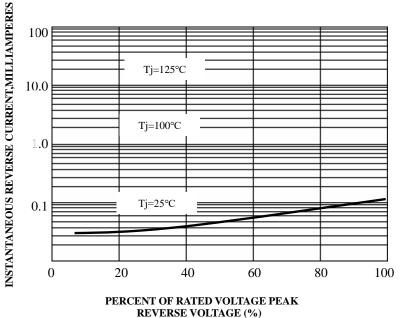
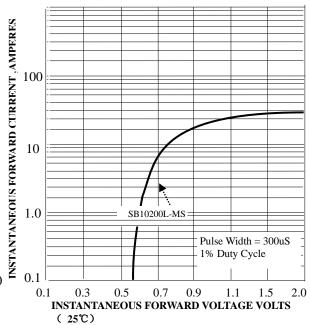
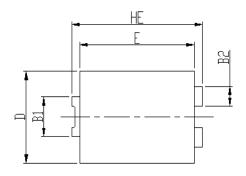


FIG. 4- TYPICAL INSTANTANEOUS FORWARD CHARCTERISTICS

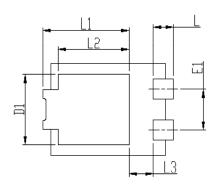




TO-277 Package Outline Dimensions

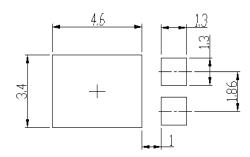






| DIM | DIM Unit: mm | | Unit: inch | |
|-------|--------------|-----|------------|-------|
| DIIVI | MIN | MAX | MIN | MAX |
| HE | 6.4 | 6.6 | 0.252 | 0.260 |
| Е | 5.6 | 5.8 | 0.220 | 0.228 |
| D | 4.1 | 4.3 | 0.161 | 0.169 |
| B1 | 1.7 | 1.9 | 0.067 | 0.075 |
| B2 | 0.8 | 1 | 0.031 | 0.039 |
| Α | 1.05 | 1.2 | 0.041 | 0.047 |
| С | 0.3 | 0.4 | 0.012 | 0.016 |
| L | 0.85 | 1.1 | 0.033 | 0.043 |
| L1 | 4.2 | 4.4 | 0.165 | 0.173 |
| L2 | 3.52 Typ. | | 0.139 Тур. | |
| L3 | 1.1 | 1.4 | 0.043 | 0.055 |
| D1 | 3 | 3.3 | 0.118 | 0.130 |
| E1 | 1.86 Typ. | | 0.073 Typ. | |

Suggested Pad Layout



Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

Order information

| Orderable Device | Package | Packing Option |
|------------------|---------|----------------|
| SB10200L-MS | TO-277 | 5000PCS |



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